# **Vishay Siliconix**

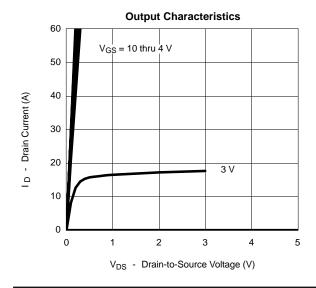


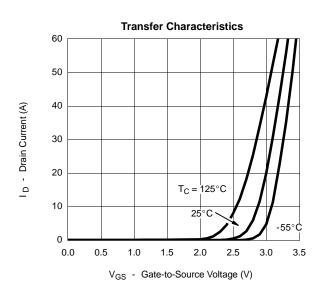
SPECIFICATIONS (T <sub>J</sub> = 25°C UNLESS OTHERWISE NOTED)						
Parameter	Symbol	Test Condition	Min	Тур	Max	Unit
Static	•		•	•	•	
Gate Threshold Voltage	V <sub>GS(th)</sub>	$V_{DS} = V_{GS}, I_D = 250 \mu A$	1.0	1.95	3.0	V
Gate-Body Leakage	I <sub>GSS</sub>	$V_{DS}$ = 0 V, $V_{GS}$ = $\pm 20$ V			±100	nA
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	$V_{DS} = 24 \text{ V}, V_{GS} = 0 \text{ V}$			1	μΑ
		$V_{DS} = 24 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 55^{\circ}\text{C}$			5	
On-State Drain Current <sup>a</sup>	I <sub>D(on)</sub>	$V_{DS} \ge 5 \text{ V}, V_{GS} = 10 \text{ V}$	30			Α
Drain-Source On-State Resistance <sup>a</sup>	「DS(on)	$V_{GS} = 10 \ V, I_D = 25 A$		0.0035	0.0045	Ω
		$V_{GS} = 4.5 \text{ V}, I_D = 19 \text{ A}$		0.0043	0.0055	
Forward Transconductance <sup>a</sup>	9 <sub>fs</sub>	$V_{DS} = 15 \text{ V}, I_{D} = 25 \text{ A}$		95		S
Diode Forward Voltage <sup>a</sup>	V <sub>SD</sub>	$I_S = 2.9 \text{ A}, V_{GS} = 0 \text{ V}$		0.72	1.1	V
Dynamic <sup>b</sup>						
Total Gate Charge	$Q_g$	$V_{DS} = 15 \text{ V}, \ V_{GS} = 4.5 \text{ V}, \ I_D = 25 \text{ A}$		34	50	nC
Gate-Source Charge	Q <sub>gs</sub>			15		
Gate-Drain Charge	Q <sub>gd</sub>			10		
Gate Resistance	Rg		0.5	1.3	2.0	Ω
Turn-On Delay Time	t <sub>d(on)</sub>	$V_{DD}$ = 15 V, $R_L$ = 15 $\Omega$ $I_D \cong$ 1 A, $V_{GEN}$ = 10 V, $R_G$ = 6 $\Omega$		21	35	ns
Rise Time	t <sub>r</sub>			15	25	
Turn-Off Delay Time	t <sub>d(off)</sub>			100	150	
Fall Time	t <sub>f</sub>			30	45	
Source-Drain Reverse Recovery Time	t <sub>rr</sub>	I <sub>F</sub> = 2.9 A, di/dt = 100 A/μs		50	80	1

#### Notes

- a. Pulse test; pulse width  $\leq 300~\mu s$ , duty cycle  $\leq 2\%$ . b. Guaranteed by design, not subject to production testing.

## TYPICAL CHARACTERISTICS (25°C UNLESS NOTED)

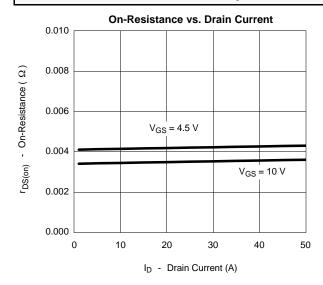


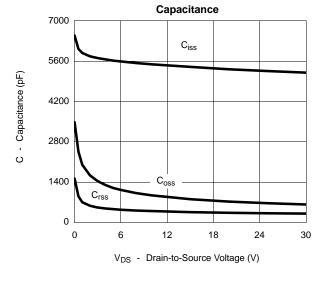


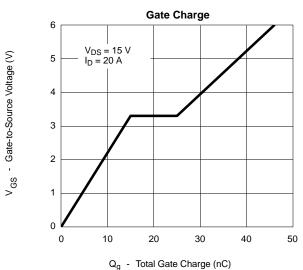


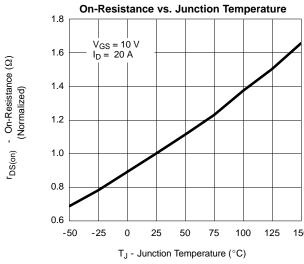
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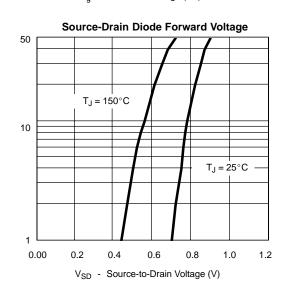
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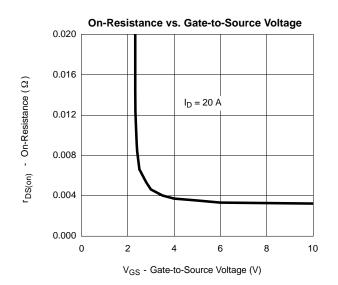










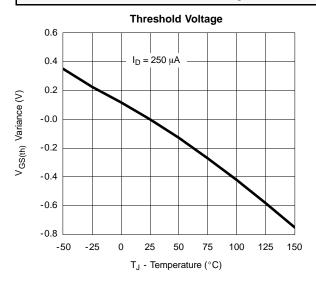


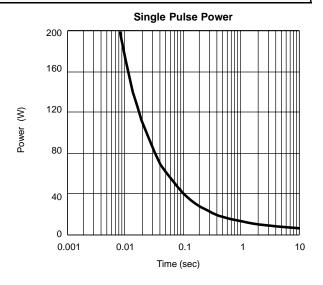
Is - Source Current (A)

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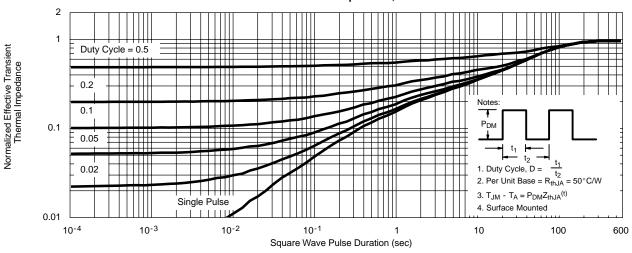


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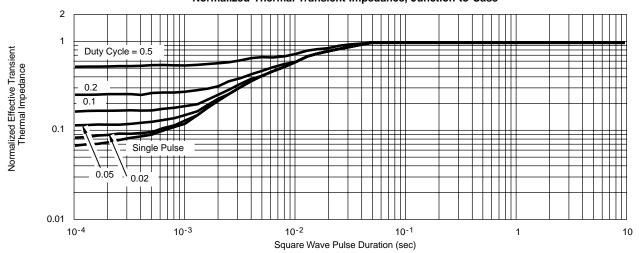




#### Normalized Thermal Transient Impedance, Junction-to-Ambient



#### Normalized Thermal Transient Impedance, Junction-to-Case





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